

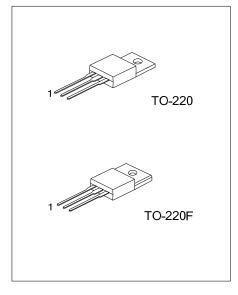
2SD313

NPN SILICON TRANSISTOR

NPN EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The UTC 2SD313 is designed for use in general purpose amplifier and switching applications.



ORDERING INFORMATION

| Ordering Number | | Dookogo | Pin Assignment | | | Dealing | |
|-----------------|-----------------|---------|----------------|---|---|---------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| 2SD313L-x-TA3-T | 2SD313G-x-TA3-T | TO-220 | В | С | Е | Tube | |
| 2SD313L-x-TF3-T | 2SD313G-x-TF3-T | TO-220F | В | С | Е | Tube | |

| 2SD313L-x-TA3-T | | |
|-----------------|-----------------|--|
| | (1)Packing Type | (1) T: Tube |
| | (2)Package Type | (2) TA3: TO-220, TF3: TO-220F |
| | (3)Rank | (3) x: refer to Classification of h_{FE} |
| | (4)Lead Free | (4) G: Halogen Free, L: Lead Free |
| | | |

■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------------|------------------|------------|------|
| Collector-Base Voltage | V _{CBO} | 60 | V |
| Collector-Emitter Voltage | V _{CEO} | 60 | V |
| Emitter-Base Voltage | V _{EBO} | 5 | V |
| Collector Current | lc | 3 | А |
| Junction Temperature | TJ | +150 | °C |
| Storage Temperature | T _{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS(Ta=25°C)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|----------------------|---|----------|-----|-----|------|
| Collector-Base Breakdown Voltage | ВV _{сво} | I _C =1mA | 60 | | | V |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | I _C =10mA | 60 | | | V |
| Emitter-Base Breakdown Voltage | BV _{EBO} | I _E =100uA | 5 | | | V |
| Collector Cut-Off Current | I _{CBO} | $V_{CB}=20V, I_{E}=0$ | | | 0.1 | mA |
| Emitter Cut-Off Current | I _{EBO} | $V_{EB}=4V$, $I_{C}=0$ | | | 1.0 | mA |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | I _C =2A, I _B =0.2A | | | 1.0 | V |
| Base-Emitter On voltage | V _{BE(ON)} | $V_{CE}=2V$, $I_{C}=1A$ | | | 1.5 | V |
| DC Current Gain | h _{FE} | I _C =1A, V _{CE} =2V I _C =0.1A,V _{CE} =2V | 40 40 | | 320 | |

CLASSIFICATION ON h_{FE}

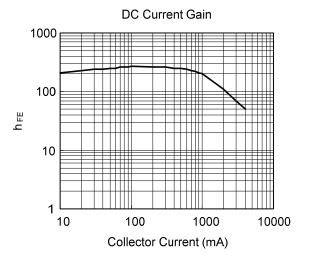
| RANK | С | D | E | F |
|-------|-------|--------|---------|---------|
| RANGE | 40-80 | 60-120 | 100-200 | 160-320 |

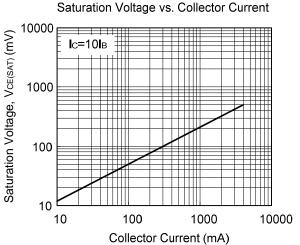


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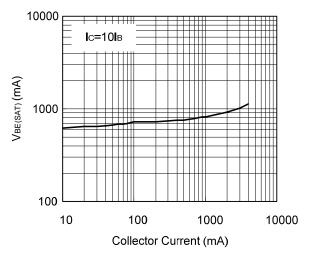
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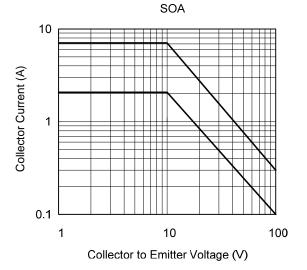
TYPICAL CHARACTERISTICS

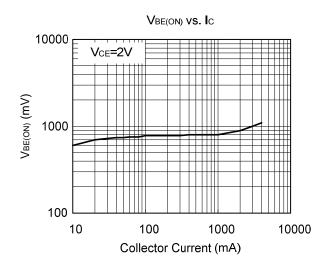


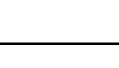












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